IXYS

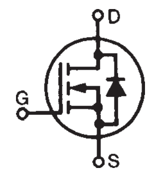
HiPerFET™ Power MOSFETs
Q-Class

IXFB 72N55Q2

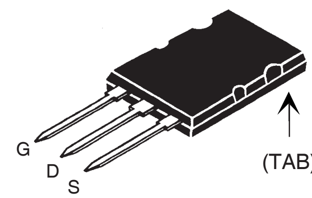
V_{DSS} = 550 V
I_{D25} = 72 A
$R_{DS(on)}$ = 72 mΩ
t_{rr} ≤ 250 ns

N-Channel Enhancement Mode
Avalanche Rated, Low Q_g, Low Intrinsic R_g
High dV/dt, Low t_{rr}

Preliminary Data Sheet



PLUS 264™ (IXFB)



G = Gate D = Drain
S = Source TAB = Drain

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	T_J = 25°C to 150°C	550	V
V_{DGR}	T_J = 25°C to 150°C; R_{GS} = 1 MΩ	550	V
V_{GS}	Continuous	±30	V
V_{GSM}	Transient	±40	V
I_{D25}	T_C = 25°C	72	A
I_{DM}	T_C = 25°C, pulse width limited by T_{JM}	284	A
I_{AR}	T_C = 25°C	72	A
E_{AR}	T_C = 25°C	60	mJ
E_{AS}	T_C = 25°C	5.0	J
dv/dt	$I_S \le I_{DM}$, di/dt ≤ 100 A/µs, $V_{DD} \le V_{DSS}$ T_J ≤ 150°C, R_G = 2 Ω	20	V/ns
P_D	T_C = 25°C	890	W
T_J		-55 ... +150	°C
T_{JM}		150	°C
T_{stg}		-55 ... +150	°C
T_L	1.6 mm (0.063 in.) from case for 10 s	300	°C
F_c	Mounting Force	30...120/7.5...27 N/lb	
Weight		10	g

Symbol	Test Conditions		Characteristic Values (T_J = 25°C, unless otherwise specified) min.	typ.	max.
V_{DSS}	V_{GS} = 0 V, I_D = 1mA		550		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, I_D = 8mA		2.5		5.0 V
I_{GSS}	V_{GS} = ±30 V, V_{DS} = 0				±200 nA
I_{DSS}	$V_{DS} = V_{DSS}$ V_{GS} = 0 V	T_J = 25°C T_J = 125°C			100 µA 5 mA
$R_{DS(on)}$	V_{GS} = 10 V, I_D = 0.5 • I_{D25} Note 1				72 mΩ

Features

- Double metal process for low gate resistance
- Unclamped Inductive Switching (UIS) rated
- Low package inductance
  - easy to drive and to protect
- Fast intrinsic rectifier

Applications

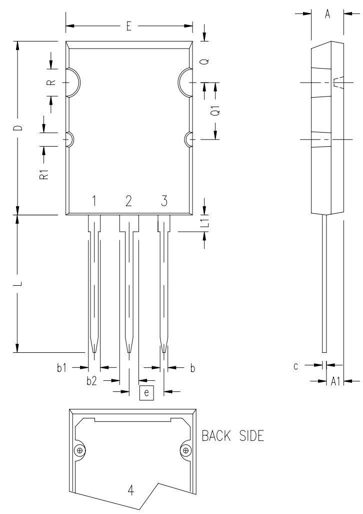
- DC-DC converters
- Switched-mode and resonant-mode power supplies, >500kHz switching
- DC choppers
- Pulse generation
- Laser drivers

Advantages

- PLUS 264™ package for clip or spring mounting
- Space savings
- High power density

Symbol	Test Conditions		Characteristic Values (T_J = 25°C, unless otherwise specified) min.	typ.	max.	
g_{fs}	V_{DS} = 10 V; I_D = 0.5 • I_{D25}	Note 1	40	57		S
C_{iss}	V_{GS} = 0 V, V_{DS} = 25 V, f = 1 MHz			10500		pF
C_{oss}				1500		pF
C_{rss}				230		pF
$t_{d(on)}$	V_{GS} = 10 V, V_{DS} = 0.5 • V_{DSS}, I_D = 0.5 • I_{D25}			30		ns
t_r	R_G = 1 Ω (External)			23		ns
$t_{d(off)}$				58		ns
t_f				10		ns
$Q_{g(on)}$	V_{GS} = 10 V, V_{DS} = 0.5 • V_{DSS}, I_D = 0.5 • I_{D25}			258		nC
Q_{gs}				65		nC
Q_{gd}				123		nC
R_{thJC}					0.14	K/W
R_{thCK}				0.13		K/W

PLUS 264™ Outline



Terminals: 1 - Gate
2 - Drain (Collector)
3 - Source (Emitter)
4 - Drain (Collector)

SYM	INCHES MIN	MAX
A	.185	.209
A1	.102	.118
b	.037	.055
b1	.087	.102
b2	.110	.126
c	.017	.029
D	1.007	1.047
E	.760	.799
e	.215 BSC	
L	.779	.842
L1	.087	.102
Q	.240	.256
Q1	.330	.346
ØR	.155	.187
ØR1	.085	.093

Source-Drain Diode

Symbol	Test Conditions	Characteristic Values (T_J = 25°C, unless otherwise specified) min.	typ.	max.	
I_S	V_{GS} = 0 V			72	A
I_{SM}	Repetitive; pulse width limited by T_{JM}			288	A
V_{SD}	$I_F = I_S$, V_{GS} = 0 V, Note 1			1.5	V
t_{rr}	I_F = 25A, -di/dt = 100 A/µs, V_R = 100 V			250	ns
Q_{RM}			1.2		µC
I_{RM}			8		A

Note: 1. Pulse test, t ≤ 300 µs, duty cycle d ≤ 2 %

Fig. 1. Output Characteristics @ 25 Deg. C

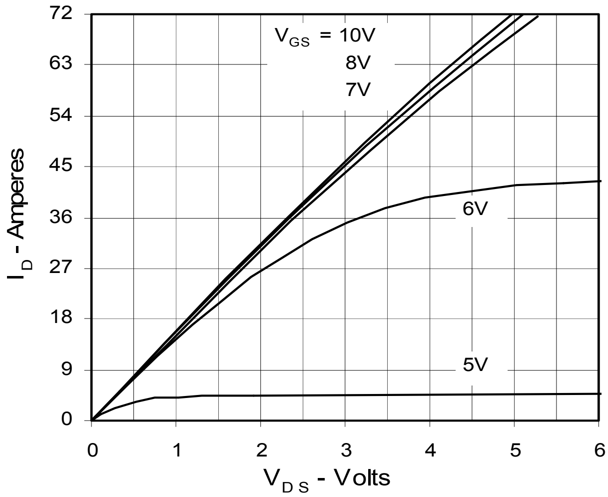


Fig. 2. Extended Output Characteristics @ 25 deg. C

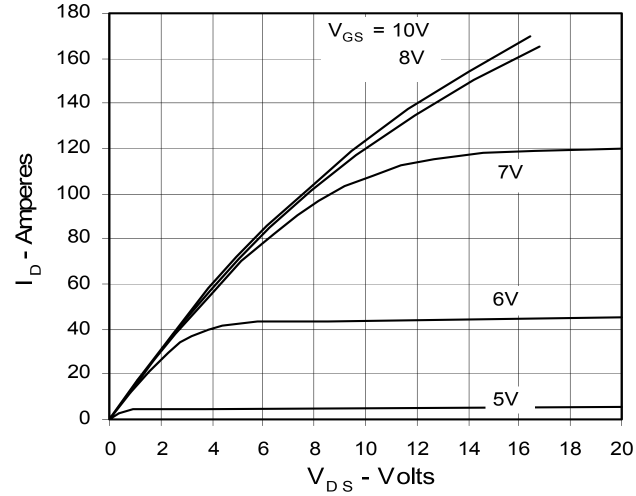


Fig. 3. Output Characteristics @ 125 Deg. C

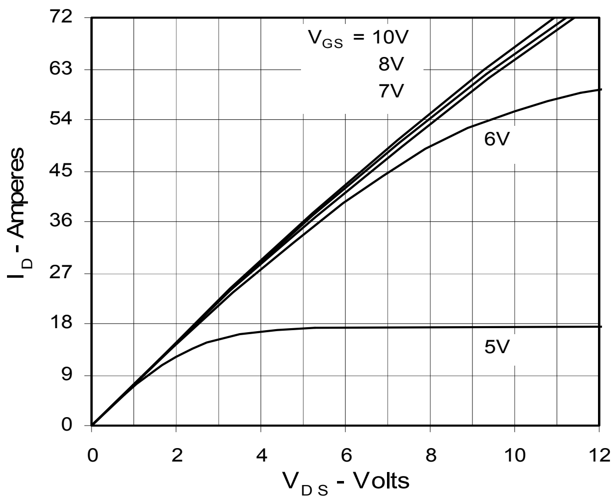


Fig. 4. $R_{DS(on)}$ Normalized to I_{D25} Value vs. Junction Temperature

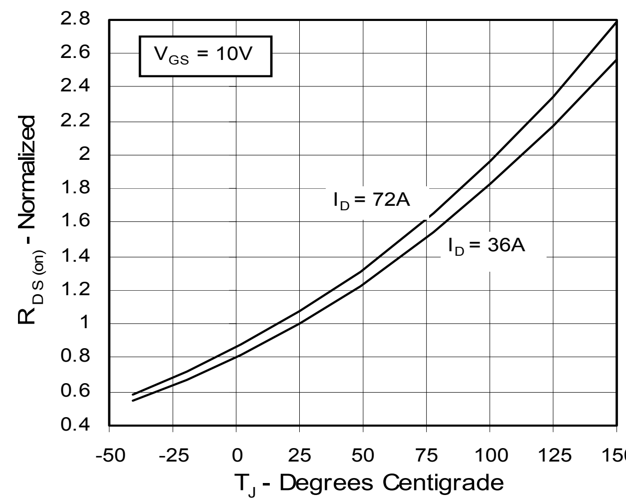


Fig. 5. $R_{DS(on)}$ Normalized to I_{D25} Value vs. I_D

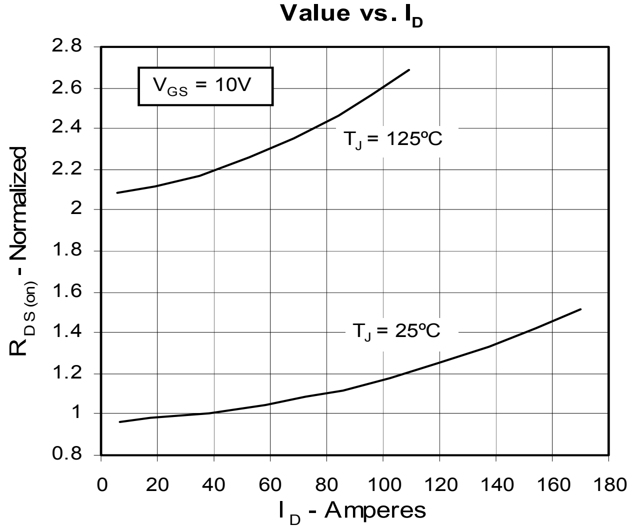


Fig. 6. Drain Current vs. Case Temperature

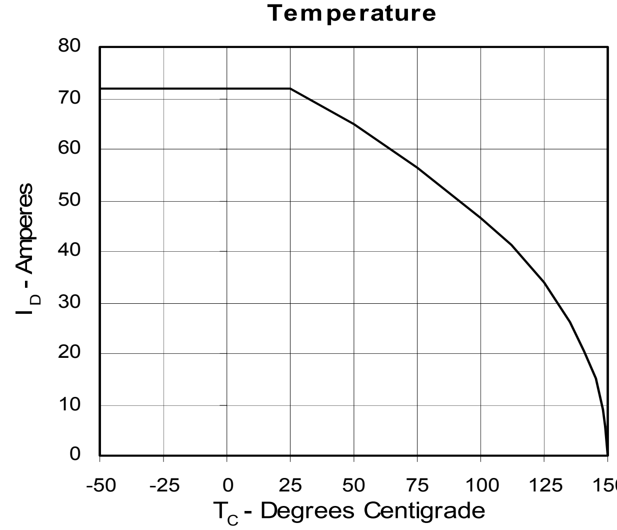


Fig. 7. Input Admittance

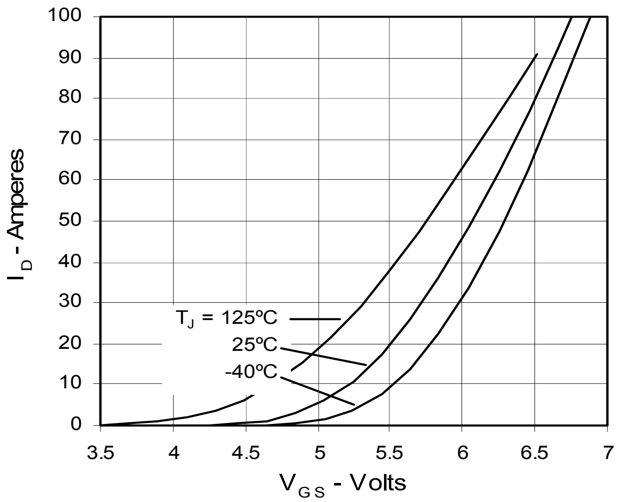


Fig. 8. Transconductance

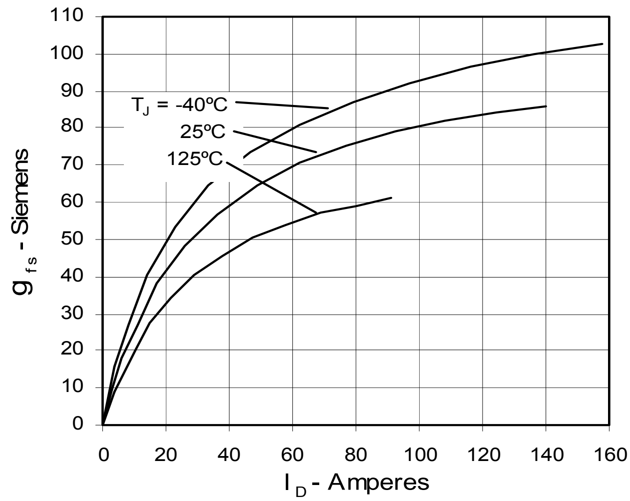


Fig. 9. Source Current vs. Source-To-Drain Voltage

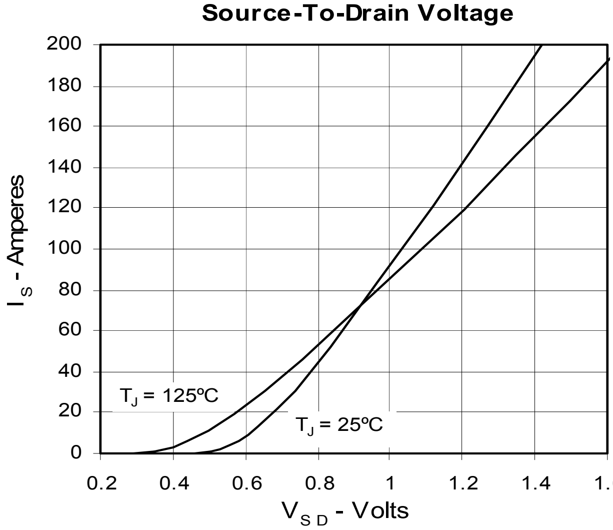


Fig. 10. Gate Charge

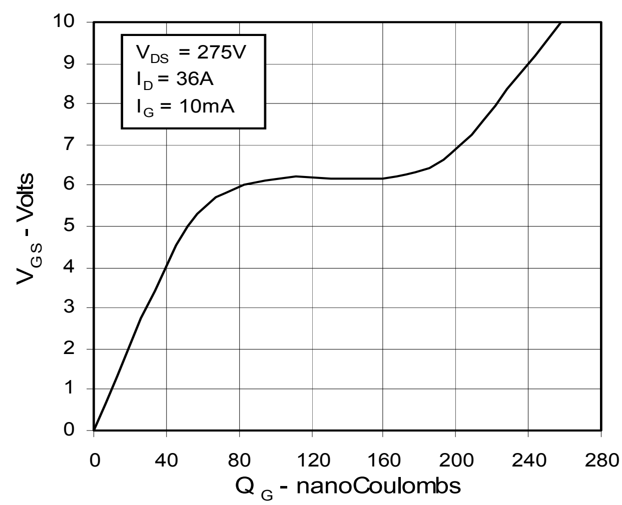


Fig. 11. Capacitance

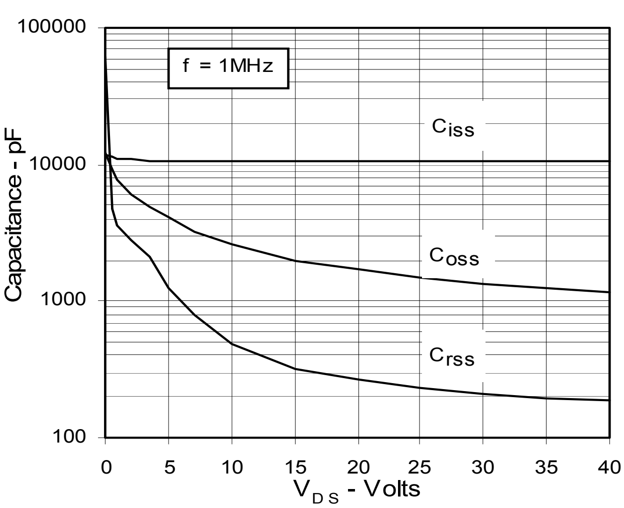


Fig. 12. Maximum Transient Thermal Resistance